

isc Silicon NPN Power Transistors
ISCM1848
DESCRIPTION

- Excellent Safe Operating Area
- High DC current Gain
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high power audio, disk head positioners and other linear applications

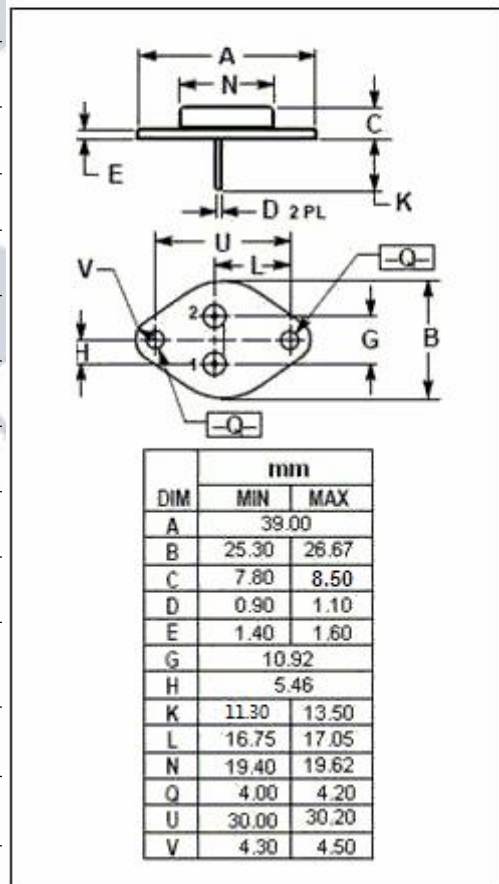
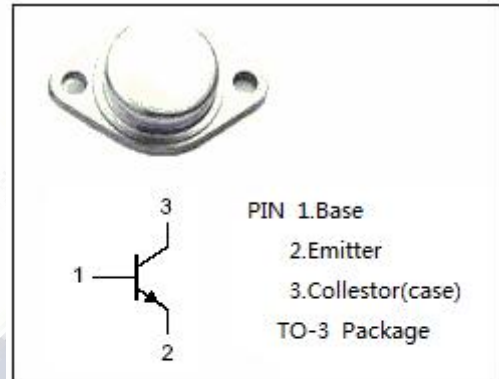
ABSOLUTE MAXIMUM RATINGS(T_c=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	250	V
V _{CEO}	Collector-Emitter Voltage	200	V
V _{EB0}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	20	A
I _{CM} (1)	Collector Current-Peak	30	A
P _D	Total Power Dissipation @T _c =25°C	200	W
T _j	Junction Temperature	-55~200	°C
T _{stg}	Storage Temperature	-55~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.68	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



isc Silicon NPN Power Transistors**ISCM1848****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)} (1)	Collector-Emitter Sustaining Voltage	I _C = 30mA ; I _B = 0	200		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 0.8A		1.3	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 16A; I _B = 3.2A		3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 8A ; V _{CE} = 4V		2.2	V
I _{CEO}	Collector Cutoff Current	V _{CE} = 200V; I _B = 0		0.5	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 250V; I _E = 0		0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0		0.1	mA
h _{FE-1}	DC Current Gain	I _C = 8A ; V _{CE} = 4V	60	120	
h _{FE-2}	DC Current Gain	I _C = 16A ; V _{CE} = 4V	15		

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle < 2%.